



MJD32CQ

#### 100V PNP HIGH VOLTAGE TRANSISTOR IN TO252

## **Description**

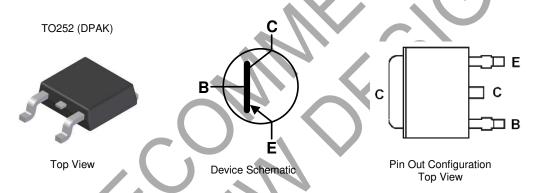
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

### **Features**

- BV<sub>CEO</sub> > -100V
- I<sub>C</sub> = -3A high Continuous Collector Current
- I<sub>CM</sub> = -5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary NPN Type: MJD31CQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.34 grams (Approximate)



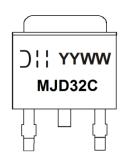
### Ordering Information (Notes 4 & 5

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD32CQ-13	Automotive	MJD32C	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



MJD32C = Product Type Marking Code

Oli = Manufacturers' code marking

YYWW = Date Code Marking

YY = Last Digit of Year (ex: 16 = 2016)

WW = Week Code (01 - 53)



# **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-100	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Collector Current	I <sub>CM</sub>	-5	Α
Continuous Base Current	I <sub>B</sub>	-1	А
Power Dissipation	P <sub>D</sub>	15	W

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Davis Diagination	(Note 6)		3.9	
Power Dissipation	(Note 7) (Note 8)	P <sub>D</sub>	2.1	W
	(Note 6)		32	
Thermal Resistance, Junction to Ambient Air	(Note 7) (Note 8)	Reja	59 80	°C/W
Thermal Resistance, Junction to Leads	(Note 8)	RejL	8.4	
Operating and Storage Temperature Range		TJ, T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 10)

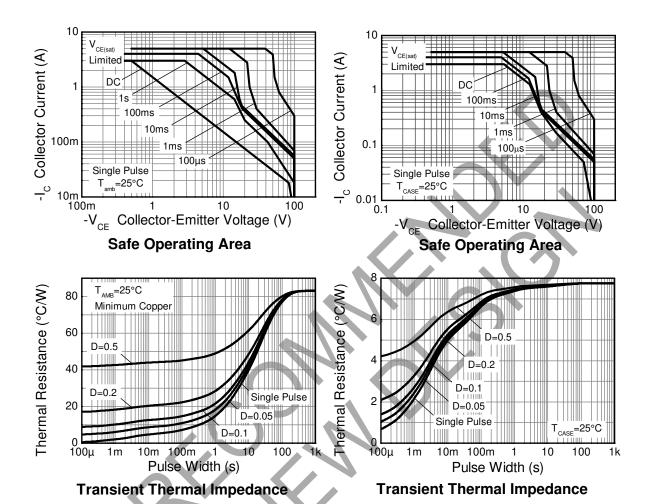
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm × 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
  8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
  9. Thermal resistance from junction to solder-point (on the exposed collector pad).
  10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics**





# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

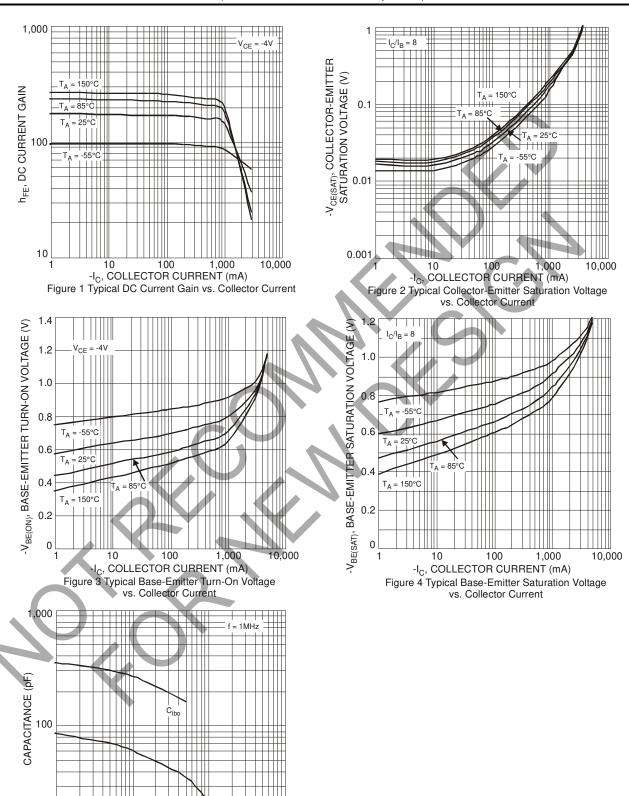
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-100			V	$I_C = -30 \text{mA}, I_B = 0$
Collector Cut-off Current	ICEO	_		-1	μΑ	$V_{CB} = -60V, I_B = 0$
Collector Cut-off Current	I <sub>CES</sub>	_	_	-1	μΑ	$V_{CE} = -100V, V_{EB} = 0$
Emitter Cut-off Current	I <sub>EBO</sub>	_	_	-1	μΑ	$V_{EB} = -5V, I_C = 0$
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	_	_	-1.2	V	$I_C = -3.0A$ , $I_B = -375mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	_	_	-1.8	V	$I_{C} = -3A$ , $V_{CE} = -4V$
DC Current Gain (Note 11)	h <sub>FE</sub>	25 10	_	<del></del> 50		V <sub>CE</sub> = -4V, I <sub>C</sub> = -1A V <sub>CE</sub> = -4V, I <sub>C</sub> = -3A
Current Signal Current Gain	H <sub>fe</sub>	20	_	_		$V_{CE} = -10V$ , $I_{C} = -0.5A$ , $f = 1KHz$
Current Gain-Bandwidth Product	f⊤	3.0	_	_	MHz	$I_C = -500$ mA, $V_{CE} = -10$ V, $f = 1$ MHz

Note: 11. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .





#### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



100

V<sub>R</sub>, REVERSE VOLTAGE (V)
Figure 5 Typical Capacitance Characteristics

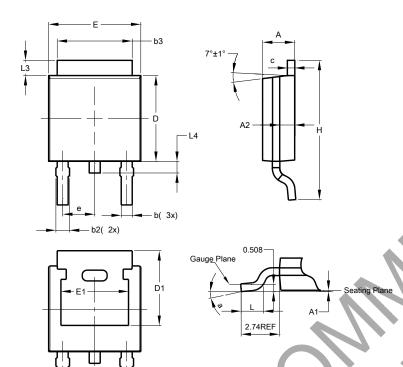
10

10 \_\_\_



# **Package Outline Dimensions**

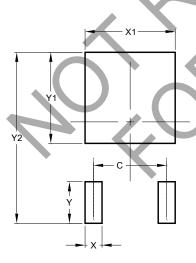
Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	,		
D1 e	5.21	-	2.286		
	5.21 - 6.45	6.70	2.286 6.58		
е	-	- - 6.70 -			
e E	- 6.45	- 6.70 - 10.41			
e E E1	- 6.45 4.32	<b>/</b> -	6.58		
e E E1	6.45 4.32 9.40	- 10.41	6.58 - 9.91		
e E E1 H	6.45 4.32 9.40 1.40	- 10.41 1.78	6.58 - 9.91 1.59		
e E E1 H L	6.45 4.32 9.40 1.40 0.88	10.41 1.78 1.27	6.58 - 9.91 1.59 1.08		

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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